

1 Scope

The present specifications shall apply to Sanken silicon diode, RM1C.

2 Outline

Type	Silicon Rectifier Diode (Mesa type)
Structure	Resin Molded Flammability: UL94V-0 (Equivalent)
Applications	Commercial Frequency Rectification, etc

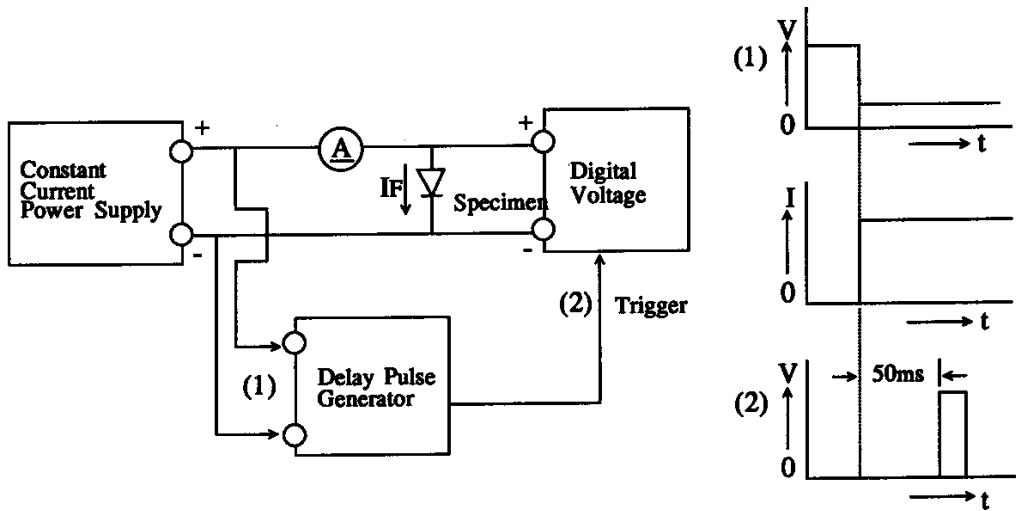
3 Absolute maximum ratings

	Transient Peak Reverse Voltage	Symbol	Unit	Rating	Conditions
1	Transient Peak Reverse Voltage	V_{RRM}	V	1050	
2	Peak Reverse Voltage	V_{RM}	V	1000	
3	Peak Reverse Current	$I_{R(AV)}$	A	0.8	Refer to derating curve in Section 6
4	Peak Surge Forward Current	I_{FSM}	A	40	10ms. Half sine wave, one shot
5	Junction Temperature	T_j	°C	-40 to +150	
6	Storage Temperature	T_{stg}	°C	-40 to +150	

4 Electrical characteristics (Ta=25°C, unless otherwise specified)

No.	Item	Symbol	Unit	Rating	Conditions
1	Forward Voltage Drop	V_F	V	1.2 max.	$I_F=1.0A$
2	Reverse Leakage Current	I_R	μA	5 max.	$V_R=V_{RM}$
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	μA	100 max.	$V_R=V_{RM}$, $T_j=100^\circ C$
4	Thermal Resistance	$R_{th(j-l)}$	°C/W	15 max.	Between Junction and Lead

5 V_F test and test circuit



6 Derating

Derating to the ambient temperature.
Power loss generated by voltage is not taken into consideration.

